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DOCKET NO. MICHEJDA 4-6

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

John A. Michejda, *et al.*

Serial No.: 09/882,911

Filed: June 15, 2001

For: A SEMICONDUCTOR DEVICE HAVING A GHOST SOURCE
DRAIN REGION AND A METHOD OF MANUFACTURE
THEREFOR

Group No.: 2815

Examiner: Fenty, Jesse A.

Honorable Commissioner of Patents
Washington, D.C. 20231

I hereby certify that this correspondence is being deposited with the United States Postal Service
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Ellen D. Schumacher
(Printed or typed name of person signing the certificate)

Ellen D. Schumacher
(Signature of the person signing the certificate)

Sir:

AMENDMENT UNDER 37 C.F.R. § 1.111

In response to the Examiner's Action mailed March 14, 2002, please amend the above-
identified application as follows:

IN THE CLAIMS:

(1) Kindly rewrite Claim 1 as follows:

1. (Amended) A semiconductor device, comprising:
a channel region located in a semiconductor substrate;
a trench located adjacent a side of the channel region;

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